

Application No.: 10/676,877

AMENDMENT TO THE SPECIFICATION

Please amend the paragraph beginning on page 10, line 19 as follows:

--Subsequently, as shown in FIG. 2B, germanium (Ge) ions, for example, belonging to group IV elements are implanted into the upper portion of the semiconductor substrate 100 at an implantation energy of about 250 keV and a dose of about 1×10^{16} /cm², thereby forming an amorphous layer 104A ~~[[in]] expanding from the substrate surface to~~ a region of the semiconductor substrate 100 deeper than the p-doped channel layer 103A. Note that the group IV element used in the formation of the amorphous layer 104A may be silicon instead of germanium. As another substitute for germanium, a dopant ion exhibiting the same conductivity type as the p-doped channel layer 103A, such as an indium ion, may be used.--

Please amend the paragraph beginning on page 16, line 18 as follows:

--Subsequently, as shown in FIG. 6B, germanium (Ge) ions, for example, belonging to group IV elements are implanted into the upper portion of the semiconductor substrate 100 at an implantation energy of about 250 keV and a dose of about 1×10^{16} /cm², thereby forming an amorphous layer 104A ~~[[in]] expanding from the substrate surface to~~ a region of the semiconductor substrate 100 deeper than the p-doped channel layer 103A. Also in the second embodiment, the group IV element used in the formation of the amorphous layer 104A may be silicon instead of germanium. As another substitute for germanium, a dopant ion exhibiting the same conductivity type as the p-doped channel layer 103A, such as an indium ion, may be used.--